L Number	Hits	Search Text	DB	Time stamp
13	21	(US-6327187-\$ or US-5739569-\$ or US-6465306-\$ or US-6445030-\$ or US-6436768-\$ or US-64353083-\$ or US-6418040-\$ or US-6005809-\$ or US-4635229-\$ or US-6448137-\$ or US-6426897-\$ or US-5493141-\$).did. or (US-20020151123-\$ or US-20020060929-\$ or US-20020032891-\$ or US-20030096476-\$ or US-20030075773-\$ or US-20030067807-\$ or US-20030067809-\$).did. or (JP-2001229683-\$).did.	USPAT; US-PGPUB; JPO	2003/08/12 20:00
16	9	•••	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/12 20:00
_	116		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/16 19:42
-	25	((nitride adj3 tunnel\$3) with layer) and (hot adj3 electron)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/22 16:40
-	3	(((nitride adj3 tunnel\$3) with layer) and (hot adj3 electron)) and (charge adj3 trap\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/22 16:44
_	854	(first adj3 voltage) and (substrate adj3 ground)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/22 16:45
_	161	((first adj3 voltage) and (substrate adj3 ground)) and (second adj3 voltage) and (ground\$3 adj3 source)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/22 16:46
-	5	<pre>(((first adj3 voltage) and (substrate adj3 ground)) and (second adj3 voltage) and (ground\$3 adj3 source)) and ((hot adj3 electron) with channel) and (inject\$3 same (charge with trap\$3))</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/26 01:19
-	1756	SONOS Same (Charge with trap\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/26 01:20
_	7	SONOS and (nitride adj2 tunnel\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/26 01:21
_	7	(SONOS and (nitride adj2 tunnel\$4)) and (charge trap\$4 (first adj2 voltage) (second adj2 voltage) (first adj2 bias) (second adj2 bias) positive)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/26 01:26

-	7	(SONOS and (nitride adj2 tunnel\$4)) and	USPAT;	2002/08/26
		(charge trap\$4 (first adj2 voltage)	US-PGPUB;	01:27
		(second adj2 voltage) (first adj2 bias)	EPO; JPO;	
		(second adj2 bias) positive ground gate	DERWENT; IBM TDB	
	ا ا	substrate drain) (drain with (positive adj2 (voltage	USPAT;	2002/11/26
-	ا	bias))) and (gate with (positive adj2	US-PGPUB;	17:45
		(voltage bias))) and (subtrate with	EPO; JPO;	1
		ground\$3) and (source with gound\$3)	DERWENT;	
		groundfo, and (boards wrom gomings)	IBM TDB	
_	58434	eras\$3 and memory	USPAT;	2002/11/26
		•	US-PGPUB;	17:27
1			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	1	(eras\$3 and memory) and (nitride adj2	USPAT;	2002/11/26
		tunneling adj2 layer) and (charge near2	US-PGPUB;	17:28
		trap\$4)	EPO; JPO;	
			DERWENT;	
		/	IBM_TDB USPAT;	2002/11/26
_	1	(eras\$3 and memory) and (nitride adj2	US-PGPUB;	17:29
		tunneling adj2 layer)	EPO; JPO;	11.25
			DERWENT;	
]		IBM TDB	
-	101	(eras\$3 and memory) and ((nitride adj2	USPAT;	2002/11/26
		tunneling adj2 layer) SONOS)	US-PGPUB;	17:29
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	35	(eras\$3 and memory) and ((nitride adj2	USPAT;	2002/11/26
		tunneling adj2 layer) SONOS) and (charge	US-PGPUB;	17:31
		near2 trap\$4)	EPO; JPO;	
			DERWENT;	
	33	((eras\$3 and memory) and ((nitride adj2	IBM_TDB USPAT;	2002/11/26
-	33	tunneling adj2 layer) SONOS) and (charge	US-PGPUB;	17:32
		near2 trap\$4)) and drain and source and	EPO; JPO;	17.32
	}	substrate and gate	DERWENT;	
		Bubbolato ana gato	IBM TDB	
-	0	(drain near4 (positive adj2 (voltage	USPĀT;	2002/11/26
		potential bias))) and (gate with	US-PGPUB;	17:48
		(positive adj2 (voltage potential bias)))	EPO; JPO;	
		and (subtrate with ground\$3) and (source	DERWENT;	
		with gound\$3)	IBM_TDB	0000 /11 /06
-	2315	(drain near4 (positive adj2 (voltage	USPAT;	2002/11/26 17:49
	1	<pre>potential bias))) and (gate with (positive adj2 (voltage potential bias)))</pre>	US-PGPUB; EPO; JPO;	11:49
		(hosicine ands (noicage bocemerat miss)))	DERWENT;	
			IBM TDB	
-	n	((drain near4 (positive adj2 (voltage	USPAT;	2002/11/26
		potential bias))) and (gate with	US-PGPUB;	17:50
		(positive adj2 (voltage potential	EPO; JPO;	
		bias)))) and (source near3 ground\$3) and	DERWENT;	
		(subtrate near3 ground\$3)	IBM_TDB	
-	1044	((drain near4 (positive adj2 (voltage	USPAT;	2002/11/26
		potential bias))) and (gate with	US-PGPUB;	17:50
		(positive adj2 (voltage potential	EPO; JPO;	
		bias)))) and (source near3 ground\$3)	DERWENT; IBM TDB	
1_	0	((drain near4 (positive adj2 (voltage	USPAT;	2002/11/26
-		((drain hear4 (positive adj2 (voitage potential bias))) and (gate with	US-PGPUB;	17:50
	1	(positive adj2 (voltage potential	EPO; JPO;	
1		bias)))) and (subtrate near3 ground\$3)	DERWENT;	
		,,,,	IBM TDB	
-	469	(((drain near4 (positive adj2 (voltage	USPAT;	2002/11/26
		potential bias))) and (gate with	US-PGPUB;	17:51
	1	(positive adj2 (voltage potential	EPO; JPO;	
	1	bias)))) and (source near3 ground\$3)) and	DERWENT;	
		(substrate same ground\$3)	IBM_TDB	

-	354	(((drain near4 (positive adj2 (voltage	USPAT;	2002/11/26
	 	potential bias))) and (gate with	US-PGPUB;	17:52
	ŀ	(positive adj2 (voltage potential bias))) and (source near3 ground\$3)) and	EPO; JPO; DERWENT;	
		(substrate with ground\$3)	IBM TDB	
_	9		USPAT;	2002/11/26
		potential bias))) and (gate with	US-PGPUB;	17:56
		(positive adj2 (voltage potential	EPO; JPO;	
		bias)))) and (source near3 ground\$3)) and	DERWENT;	
		(substrate with ground\$3)) and SONOS	IBM_TDB	
-	9	, , , , , , , , , , , , , , , , , , ,	USPAT;	2002/11/26
		potential bias))) and (gate with	US-PGPUB;	17:59
		(positive adj2 (voltage potential bias))) and (source near3 ground\$3)) and	EPO; JPO; DERWENT;	
		(substrate with ground\$3)) and SONOS) and	IBM TDB	
		eras\$3	15155	
_	1190	•	USPAT;	2003/03/25
		(eras\$3 same (drain and source and gate	US-PGPUB;	12:55
		and (positive near3 (bias potential	EPO; JPO;	
		voltage)) and ground))	DERWENT;	
			IBM_TDB	
-	369		USPAT;	2003/03/25
		(eras\$3 same (drain and source and gate and (positive near3 (bias potential	US-PGPUB; EPO; JPO;	12:56
		voltage)) and ground))) and ((positive	DERWENT;	
		adj3 (bias potential voltage)) near3	IBM TDB	
		drain)		
-	616	((non-volatile nonvolatile flash) and	USPAT;	2003/03/25
		(eras\$3 same (drain and source and gate	US-PGPUB;	12:59
		and (positive near3 (bias potential	EPO; JPO;	
		voltage)) and ground))) and ((positive	DERWENT;	
		adj3 (bias potential voltage)) near3	IBM_TDB	
_	681	((non-volatile nonvolatile flash) and	USPAT;	2003/03/25
	001	(eras\$3 same (drain and source and gate	US-PGPUB;	12:56
		and (positive near3 (bias potential	EPO; JPO;	
		voltage)) and ground))) and (ground near3	DERWENT;	
		source)	IBM_TDB	
_	206	(((non-volatile nonvolatile flash) and	USPAT;	2003/03/25
		(eras\$3 same (drain and source and gate	US-PGPUB;	12:57
		and (positive near3 (bias potential voltage)) and ground))) and ((positive	EPO; JPO; DERWENT;	
		adj3 (bias potential voltage)) near3	IBM TDB	
		drain)) and (((non-volatile nonvolatile		
		flash) and (eras\$3 same (drain and source		
		and gate and (positive near3 (bias		
		potential voltage)) and ground))) and		
		((positive adj3 (bias potential voltage))		
		near3 gate)) and (((non-volatile nonvolatile flash) and (eras\$3 same		
		(drain and source and gate and (positive		
		near3 (bias potential voltage)) and		
		<pre>ground))) and (ground near3 source))</pre>		
-	69	((positive adj3 (bias potential voltage))	USPAT;	2003/03/25
		near3 drain) same (ground near3 source)	US-PGPUB;	13:04
		same ((positive adj3 (bias potential	EPO; JPO;	
		voltage)) near3 gate)	DERWENT;	
_	26	((non-volatile nonvolatile flash) and	IBM_TDB USPAT;	2003/03/25
	20	(eras\$3 same (drain and source and gate	US-PGPUB;	13:00
		and (positive near3 (bias potential	EPO; JPO;	-5.55
		voltage)) and ground))) and (((positive	DERWENT;	
		adj3 (bias potential voltage)) near3	IBM_TDB	
		drain) same (ground near3 source) same	_	
		((positive adj3 (bias potential voltage))		
_	120	near3 gate))	HCDAM -	2002/02/25
-	138	(((positive high) adj3 (bias potential voltage)) near3 drain) same (ground near3	USPAT; US-PGPUB;	2003/03/25 13:05
		source) same (((positive high) adj3 (bias	EPO; JPO;	13.03
		potential voltage)) near3 gate)	DERWENT;	
			IBM_TDB	

				<u> </u>
-	43	((non-volatile nonvolatile flash) and	USPAT;	2003/03/25 .
		(eras\$3 same (drain and source and gate	US-PGPUB;	13:05
		and (positive near3 (bias potential	EPO; JPO;	
		voltage)) and ground))) and (((positive	DERWENT;	
		high) adj3 (bias potential voltage))	IBM_TDB	
		near3 drain) same (ground near3 source)		
		same (((positive high) adj3 (bias		
		potential voltage)) near3 gate))		
-	120	(nitride adj3 tunnel\$3) near3 layer	USPAT;	2003/07/15
	•		US-PGPUB;	20:39
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	2		USPAT;	2003/07/15
		tunnel\$3) near3 layer)	US-PGPUB;	20:40
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	13	1 =	USPAT;	2003/07/15
		US-6436768-\$ or US-6418040-\$ or	US-PGPUB	20:47
		US-6327187-\$ or US-6005809-\$ or		
		US-4353083-\$ or US-4635229-\$ or		
		US-5739569-\$ or US-6448137-\$).did. or		
	1	(US-20020151123-\$ or US-20020032891-\$ or		
	1	US-20020060929-\$).did.		
-	12		USPAT;	2003/07/15
		US-6436768-\$ or US-6418040-\$ or	US-PGPUB;	20:47
		US-6327187-\$ or US-6005809-\$ or	EPO; JPO;	
		US-4353083-\$ or US-4635229-\$ or	DERWENT;	
		US-5739569-\$ or US-6448137-\$).did. or	IBM_TDB	
		(US-20020151123-\$ or US-20020032891-\$ or		
	222	US-20020060929-\$).did.) and (eras\$3)	TIGDAM.	2002/07/16
-	332	1 1 27	USPAT;	2003/07/16
		and sonos	US-PGPUB;	19:43
e.	,		EPO; JPO; DERWENT;	4
	*		IBM TDB	
	164	((nonvolatile (non adj volatile) flash)	USPAT;	2003/07/16
-	164	and sonos) and (program\$4 writ\$3) and	US-PGPUB;	19:45
		(eras\$3)	EPO; JPO;	13.43
		(elasys)	DERWENT;	
· •			IBM TDB	
	169	((nonvolatile (non adj volatile) flash)	USPAT;	2003/07/16
to the second		and sonos) and (eras\$3)	US-PGPUB;	20:24
			EPO; JPO;	
	1		DERWENT;	
1			IBM TDB	
-	36		USPAT;	2003/07/16
		and sonos) and (eras\$3 near3 method)	US-PGPUB;	20:24
		The second secon	EPO; JPO;	
1			DERWENT;	
		*	IBM_TDB	
-	2943	• •	USPAT;	2003/08/12
		(eras\$3 near3 method)	US-PGPUB;	16:32
	l		EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	374	1 ' '	USPAT;	2003/08/12
	1	(eras\$3 near3 method)) and (drain same	US-PGPUB;	16:25
		gate same (ground near3 source))	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	0	, , , , , , , , , , , , , , , , , , , ,	USPAT;	2003/08/12
		((eras\$3 near3 method) same (drain same	US-PGPUB;	16:33
		gate same (ground near3 source)))	EPO; JPO;	
			DERWENT;	
	1		IBM_TDB	1

_	<pre>(nonvolatile non-volatile flash) and ((eras\$3 near3 method) same drain same gate same (ground near3 source))</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/08/12 16:33
1		IBM_TDB	